



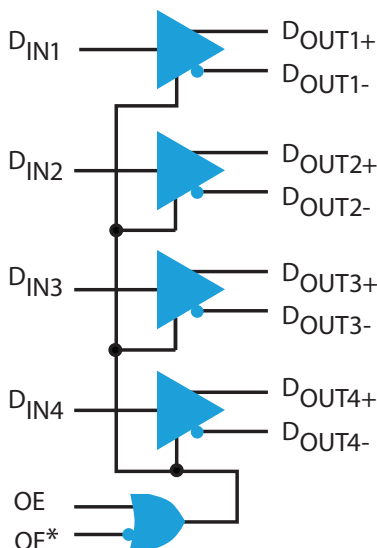
## Features

- DC to 400 Mbps / 200 MHz low noise, low skew, low power operation
  - 300 ps (max) channel-to-channel skew
  - 250 ps (max) pulse skew
  - 23 mA (max) power supply current
- LVDS outputs conform to TIA/EIA-644-A standard
- Standard output enable scheme eliminates power consumption when device is not in use
- Guaranteed operation within industrial temperature range -40° to +85°C
- Available in space saving SOIC-16 and TSSOP-16 packages
- For Point to Point Applications
- Pin and function compatible with DS90LV031A and SN65LVDS31

## Applications

- Digital Copiers
- Wireless Base Stations
- Telecom / Datacom
- Network Routing

## Function Diagram



## Description

The TF90LVDS031 is a 400 Mbps Quad LVDS (low voltage differential signaling) Line Driver optimized for high-speed, low power, low noise transmission over controlled impedance (approximately 100Ω) transmission media (e.g. cables, printed circuit board traces, backplanes).

The TF90LVDS031 accepts four LVCMOS / LVTTTL signals and translates them to four LVDS signals. Its differential outputs can be disabled and put in a high-impedance state via two enable pins, OE and OE\*.

Low 300 ps (max) channel-channel skew and 250 ps (max) pulse skew ensure reliable communication in high-speed links that are highly sensitive to timing error.

Supply current is 23 mA (max). LVDS outputs conform to the ANSI/EIA/TIA-644-A standard. The TF90LVDS031 is offered in 16-pin SOIC and TSSOP packages and operates over an extended -40 °C to +85 °C temperature range.

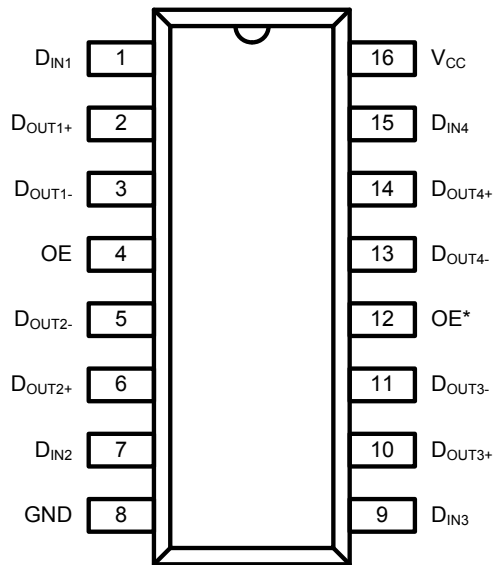


## Ordering Information

Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF90LVDS031-TBU	SOIC-16(N)	Tube / 48	TF YYWW TFS031TB Lot ID
TF90LVDS031-TBG	SOIC-16(N)	T&R / 500	TF YYWW TFS0316C Lot ID
TF90LVDS031-6CU	TSSOP-16	Tube / 94	TF YYWW TFS0316C Lot ID
TF90LVDS031-6CG	TSSOP-16	T&R / 1000	TF YYWW TFS0316C Lot ID

## Pin Diagram



SOIC-16 or TSSOP-16

## Logic Table

OE	OE*	D <sub>OUT+</sub>	D <sub>OUT-</sub>
0	0	Enabled	Enabled
0	1	Disabled	Disabled
1	0	Enabled	Enabled
1	1	Enabled	Enabled

**Table 1.** Output Enables Truth Table

## Pin Descriptions

PIN NAME	PIN NUMBER	PIN TYPE	PIN DESCRIPTION
D <sub>IN1</sub> , D <sub>IN2</sub> , D <sub>IN3</sub> , D <sub>IN4</sub>	1, 7, 9, 15	LVC MOS inputs	Driver LVC MOS input pins.
D <sub>OUT1+</sub> , D <sub>OUT1-</sub> , D <sub>OUT2+</sub> , D <sub>OUT2-</sub> , D <sub>OUT3+</sub> , D <sub>OUT3-</sub> , D <sub>OUT4+</sub> , D <sub>OUT4-</sub>	2, 3, 5, 6, 10, 11, 13, 14,	LVDS outputs	Non-inverting and inverting LVDS output pins.
OE, OE*	4, 12	LVC MOS inputs	Driver output enable pins. When OE is high or OE* is low or open, the driver outputs are enabled. When OE is low and OE* is high, the driver outputs are disabled.
V <sub>CC</sub>	16	Power	Power supply pin. Bypass V <sub>CC</sub> to GND with 0.1 μF and 0.01 μF ceramic capacitors.
GND	8	Power	Ground or circuit common pin.

## Absolute Maximum Ratings<sup>1</sup>

$V_{CC}$ to GND.....	-0.3V to +4V	TSSOP-16 Thermal Resistance	
Inputs		$\theta_{JC}$ .....	29 °C/W
OE, $D_{IN}$ to GND.....	-0.3V to $V_{CC} + 0.3V$	$\theta_{JA}$ .....	103 °C/W
Outputs		Storage Temperature Range .....	-65°C to +150°C
$D_{OUT+}$ , $D_{OUT-}$ to GND.....	-0.3V to $V_{CC} + 0.3V$	Maximum Junction Temperature .....	+150°C
Maximum Package Power Dissipation ( $T_A = +25\text{ °C}$ )		Lead Temperature (soldering, 4s) .....	+260°C
SOIC-16 (derate 13.8 mW/°C above +25 °C).....	1.7 W	ESD Ratings	
TSSOP-16 (derate 9.7 mW/°C above +25 °C).....	1.2 W	HBM <sup>1</sup> .....	8 kV
SOIC-16 Thermal Resistance		MM <sup>2</sup> .....	250V
$\theta_{JC}$ .....	41 °C/W	CDM <sup>3</sup> .....	1.25 kV
$\theta_{JA}$ .....	72 °C/W		

<sup>1</sup> Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<sup>1</sup> Human Body Model, applicable standard JESD22-A114-C  
<sup>2</sup> Machine Model, applicable standard JESD22-A115-A  
<sup>3</sup> Field Induced Charge Device Model, applicable standard JESD22-C101-C

## Recommended Operating Conditions

Symbol	Parameter	Pins	MIN	TYP	MAX	Unit
$V_{CC}$	Supply Voltage	$V_{CC}$	3	3.3	3.6	V
$V_{IH}$	High-level input voltage	OE, OE*, $D_{IN}$	2		$V_{CC}$	V
$V_{IL}$	Low-level input voltage	OE, OE*, $D_{IN}$	0		0.8	V
$T_A$	Operating free-air temperature	All	-40	25	85	°C

## Electrical Characteristics

Over recommended operating conditions (**NOTE1**), unless otherwise specified. Typical values are  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ .

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
<b>LVCMOS Specifications (OE, OE*, D<sub>IN</sub> pins)</b>						
V <sub>IH</sub>	High-level input voltage		2.0		V <sub>CC</sub>	V
V <sub>IL</sub>	Low-level input voltage		GND		0.8	V
I <sub>IH</sub>	High-level input current	V <sub>CC</sub> = 3.6V V <sub>IN</sub> = 3.6V	-10		10	μA
I <sub>IL</sub>	Low-level input current	V <sub>CC</sub> = 3.6V V <sub>IN</sub> = 0V	-10		10	μA
V <sub>CL</sub>	Input clamp voltage ( <b>NOTE2</b> )	I <sub>CL</sub> = -18 mA, V <sub>CC</sub> = 0V	-1.5	-0.9		V
<b>LVDS Output Specifications (D<sub>OUT+</sub>, D<sub>OUT-</sub> pins)</b>						
V <sub>OD</sub>	Differential output voltage magnitude	R <sub>L</sub> = 100Ω Figure 1	250	370	450	mV
ΔV <sub>OD</sub>	Change in magnitude of V <sub>OD</sub> for complimentary output states		-35		35	mV
V <sub>O<sub>CM</sub>(ss)</sub>	Steady-state output common mode voltage		1.125	1.25	1.375	V
ΔV <sub>O<sub>CM</sub>(ss)</sub>	Change in magnitude of V <sub>O<sub>CM</sub>(ss)</sub> for complimentary output states		-25		25	mV
V <sub>OH</sub>	Output high voltage	R <sub>L</sub> = 100Ω Figure 1		1.43	1.6	V
V <sub>OL</sub>	Output low voltage		0.9	1.06		V
I <sub>OS</sub>	Output short circuit current ( <b>NOTE3</b> )	Enabled, D <sub>OUT+</sub> or D <sub>OUT-</sub> = 0V			-13	mA
I <sub>OSD</sub>	Differential output short circuit current ( <b>NOTE3</b> )	Enabled, V <sub>OD</sub> = 0V			-13	mA
I <sub>OZ</sub>	High-impedance output current	Disabled, V <sub>out</sub> = 0V or V <sub>CC</sub>	-14		+14	μA
C <sub>OUT</sub>	Output capacitance	D <sub>OUT+</sub> or D <sub>OUT-</sub> to GND		3		pF
<b>Power Supply Current Specifications</b>						
I <sub>CC</sub>	Power supply current without output loads	Enabled D <sub>IN</sub> = 0V or V <sub>CC</sub>		1	2	mA
I <sub>CCL</sub>	Power supply current with output loads	Enabled D <sub>IN</sub> = 0V or V <sub>CC</sub> , R <sub>L</sub> = 100Ω		16	23	mA
I <sub>CCZ</sub>	Power supply current with disabled outputs	Disabled OE = 0 and OE* = 1		1	2	mA

**NOTE1** Current into device pin is defined as positive. Current out of the device is defined as negative. All voltages are referenced to ground, unless otherwise specified.

**NOTE2** This specification is not production tested and is guaranteed by design simulations.

**NOTE3** Output short circuit current (I<sub>OS</sub>) is specified as magnitude only. The minus sign indicates direction only.

## Switching Characteristics

Over recommended operating conditions, unless otherwise specified. Typical values are at  $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ .

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
<b>LVDS AC Specifications (Notes 4, 5 and 6)</b>						
$t_{PLH}$	Propagation delay, low-to-high	Figures 2 and 3 $R_L = 100\Omega$ $C_L = 15pF$ (Note 12)	0.6	1	1.9	ns
$t_{PHL}$	Propagation delay, high-to-low		0.6	1	1.9	ns
$t_r$	Rise time		.35	1	ns	
$t_f$	Fall time		.35	1	ns	
$t_{SK(p)}$	Pulse skew (Note 7)		50	250	ps	
$t_{SK(c-c)}$	Channel-to-channel skew (Note 8)		80	300	ps	
$t_{SK(p-p)A}$	Part-to-part skew (Note 9)			1	ns	
$t_{SK(p-p)B}$	Part-to-part skew (Note 10)			1.3	ns	
$t_{PLZ}$	Disable time, low-to-high Z	Figures 4 and 5 $R_L = 100\Omega$ $C_L = 15pF$ (Note 12)			5	ns
$t_{PHZ}$	Disable time, high-to-high Z				5	ns
$t_{PZL}$	Enable time, high Z-to-low				5	ns
$t_{PZH}$	Enable time, high Z-to-high				5	ns
$f_{MAX}$	Maximum operating frequency (Note 11)	Figure 2	200	250		MHz

**NOTE4** Generator output characteristics (unless otherwise specified):  $f = 1\text{ MHz}$ ,  $Z_0 = 50\Omega$ ,  $t_r < 1\text{ ns}$ ,  $t_f < 1\text{ ns}$ .

**NOTE5** All input voltages are for one channel unless otherwise specified. Other inputs are set to GND.

**NOTE6** Switching Characteristic specification are not production tested and are guaranteed by statistical analysis of characterization data.

**NOTE7**  $t_{SK(p)}$  pulse skew, is the magnitude difference in propagation delay time between the positive going edge and the negative going edge of the same channel ( $t_{SK(p)} = |t_{PLH} - t_{PHL}|$ ).

**NOTE8**  $t_{SK(c-c)}$  channel-to-channel skew, is the difference in propagation delay time between channels on the same device at any operating temperature and supply voltage.

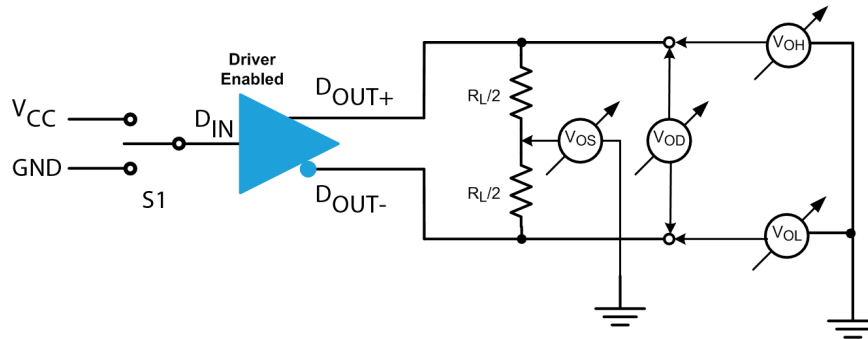
**NOTE9**  $t_{SK(p-p)A}$  part-to-part skew "A", is the difference in propagation delay time between devices operating at the same power supply voltage and within  $5^\circ C$  of each other within the operating temperature range.

**NOTE10**  $t_{SK(p-p)B}$  part-to-part skew "B", is the difference in propagation delay time between devices operating at any recommended power supply voltage and ambient temperature. It is also defined as  $|MIN - MAX|$  propagation delay ( $t_{PLH}$  or  $t_{PHL}$ ).

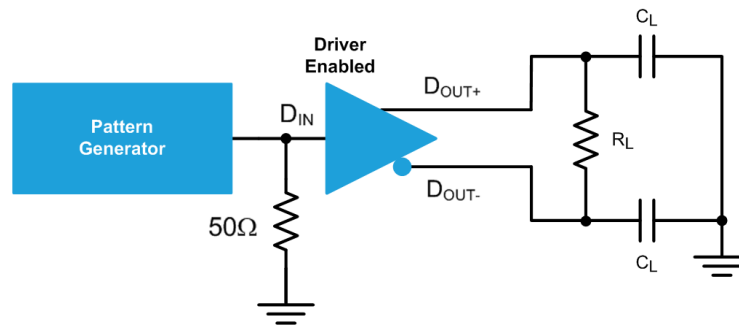
**NOTE11** Generator output characteristics for the  $f_{MAX}$ :  $Z_0 = 50\Omega$ ,  $t_r = t_f < 1\text{ ns}$ , 50% duty cycle, 0V to 3V amplitude. Output criteria for  $f_{MAX}$ : 45% / 55% duty cycle,  $V_{OD} \geq 250\text{ mV}$ .

**NOTE12** The capacitive load  $C_L$  includes test fixture, probe and lumped capacitance..

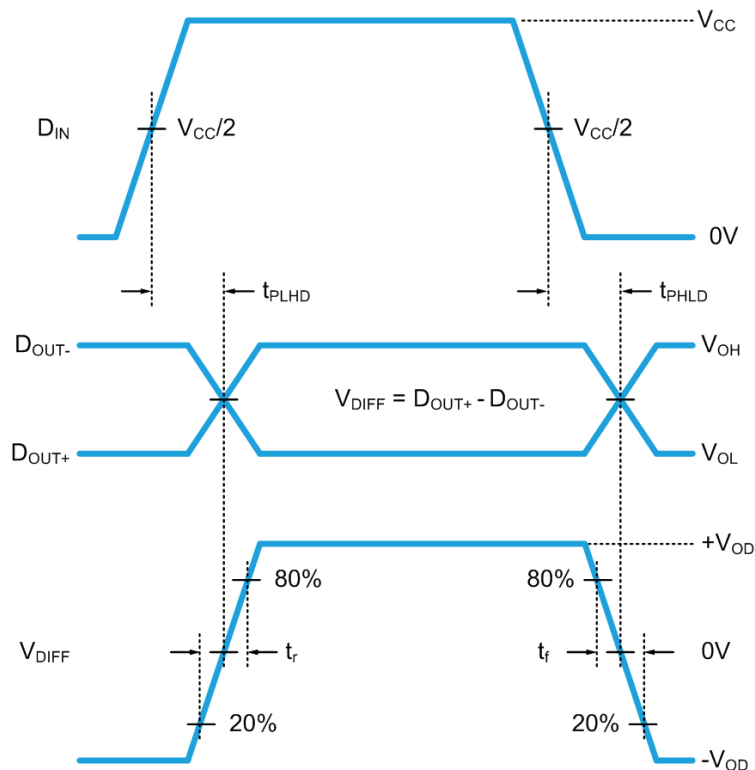
**Test Circuits and Timing Diagrams**



**Figure 1.** Driver  $V_{OH}$  and  $V_{OL}$  Test Setup

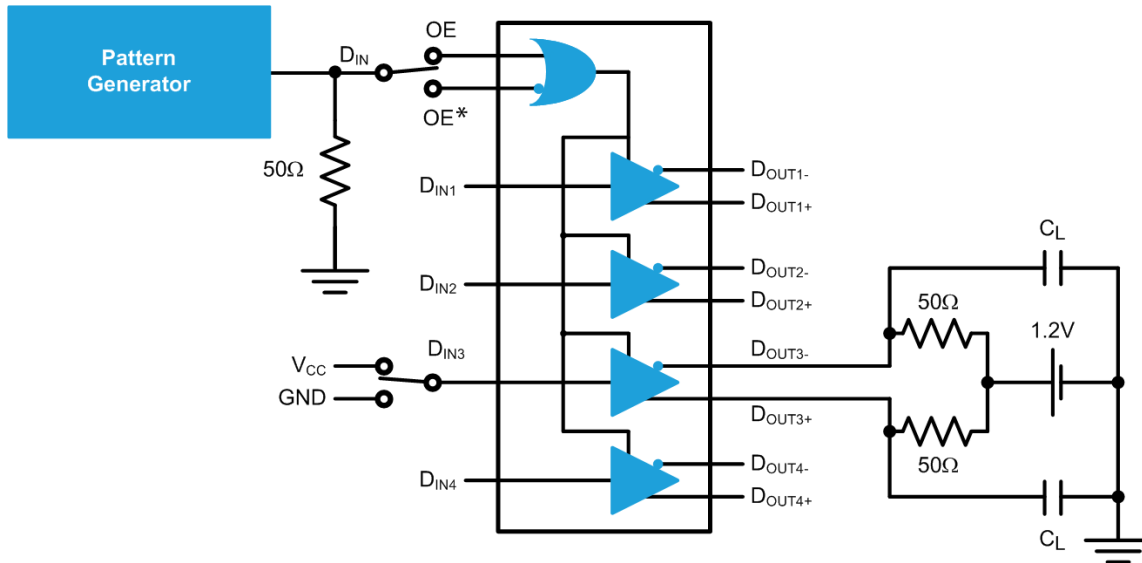


**Figure 2.** Driver Propagation Delay and Transition Time Test Setup

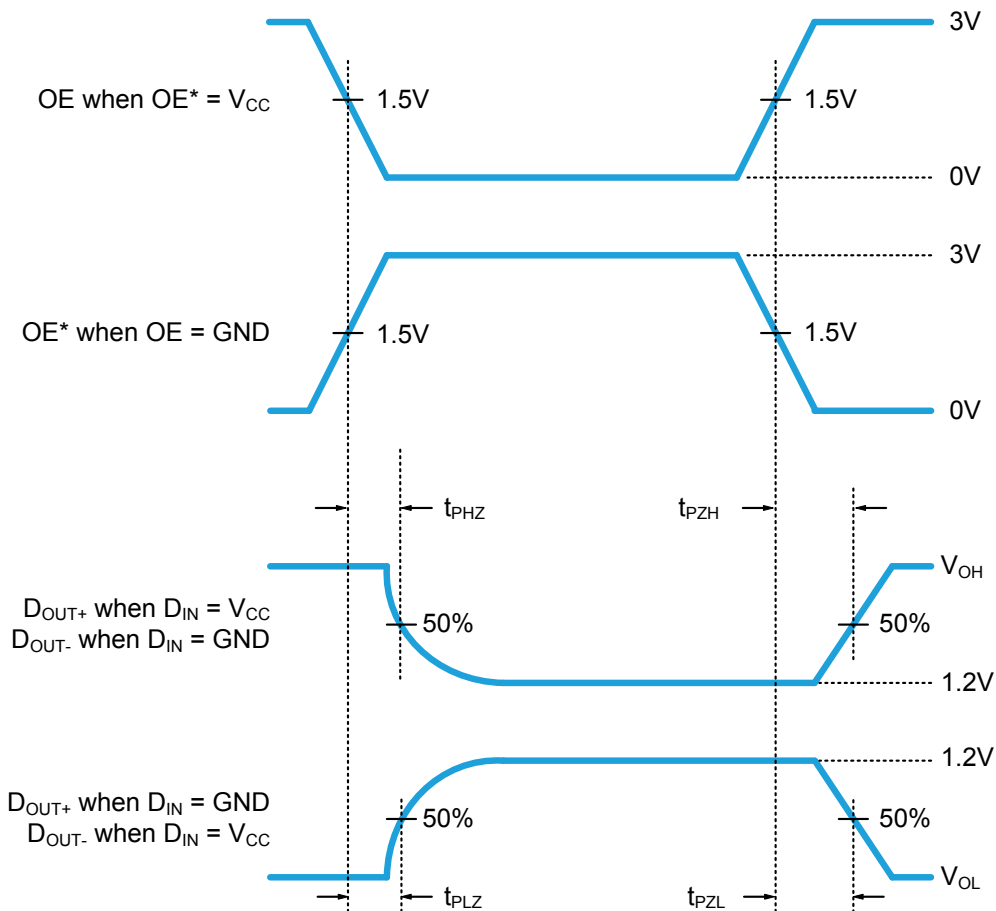


**Figure 3.** Driver Propagation Delay and Transition Time Waveforms

**Test Circuits and Timing Diagrams**

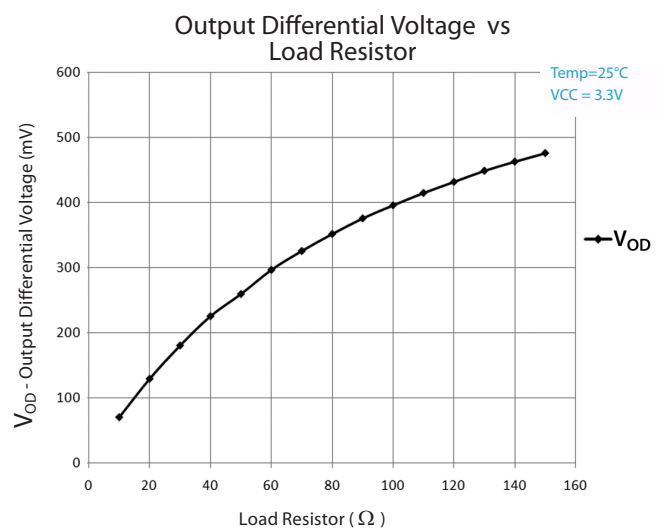
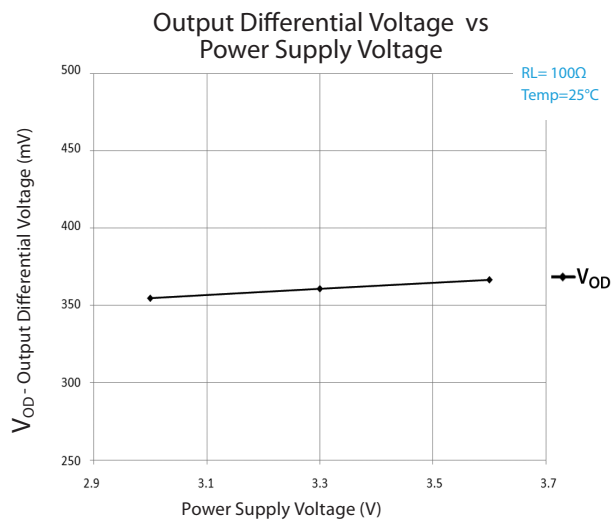
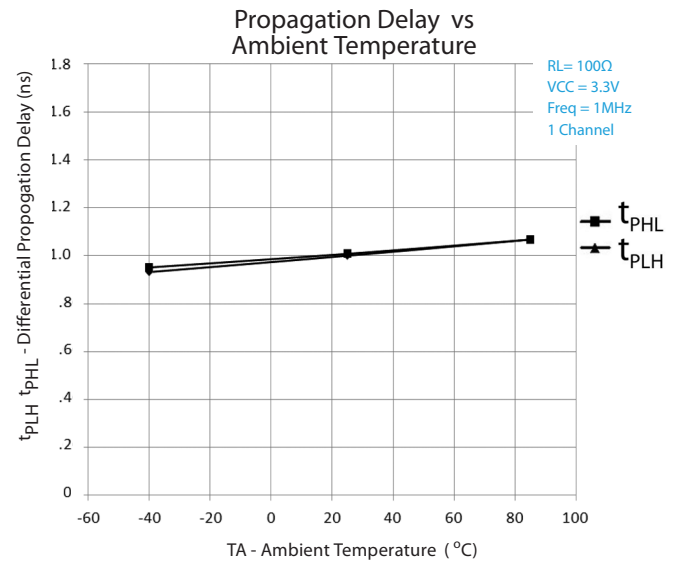
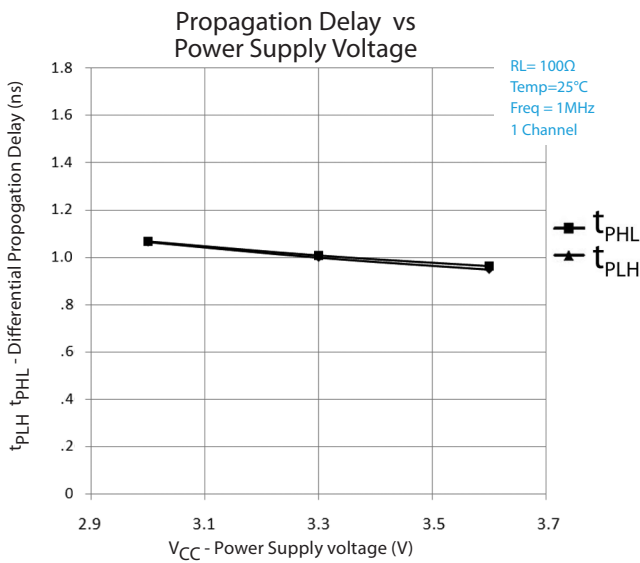
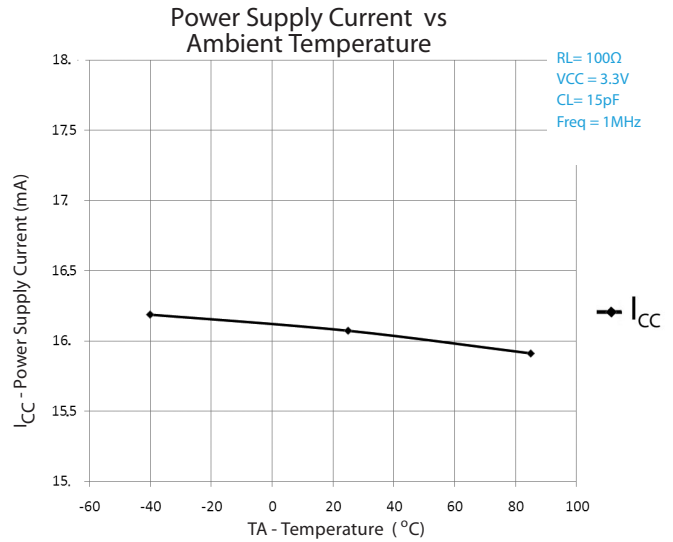
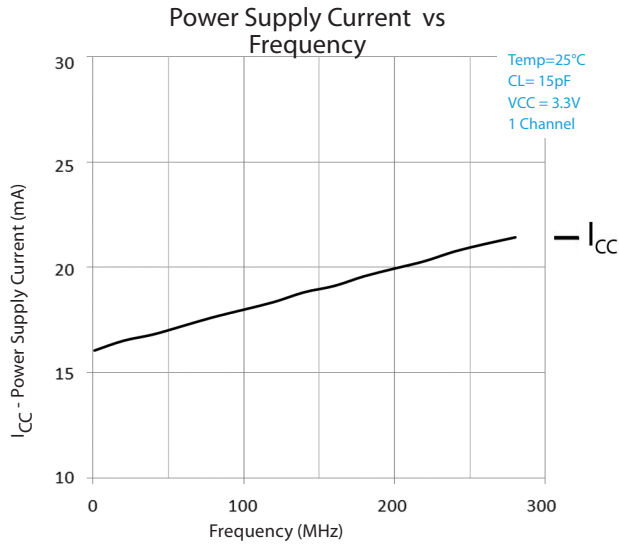


**Figure 4.** Driver High-Z Delay Test Setup

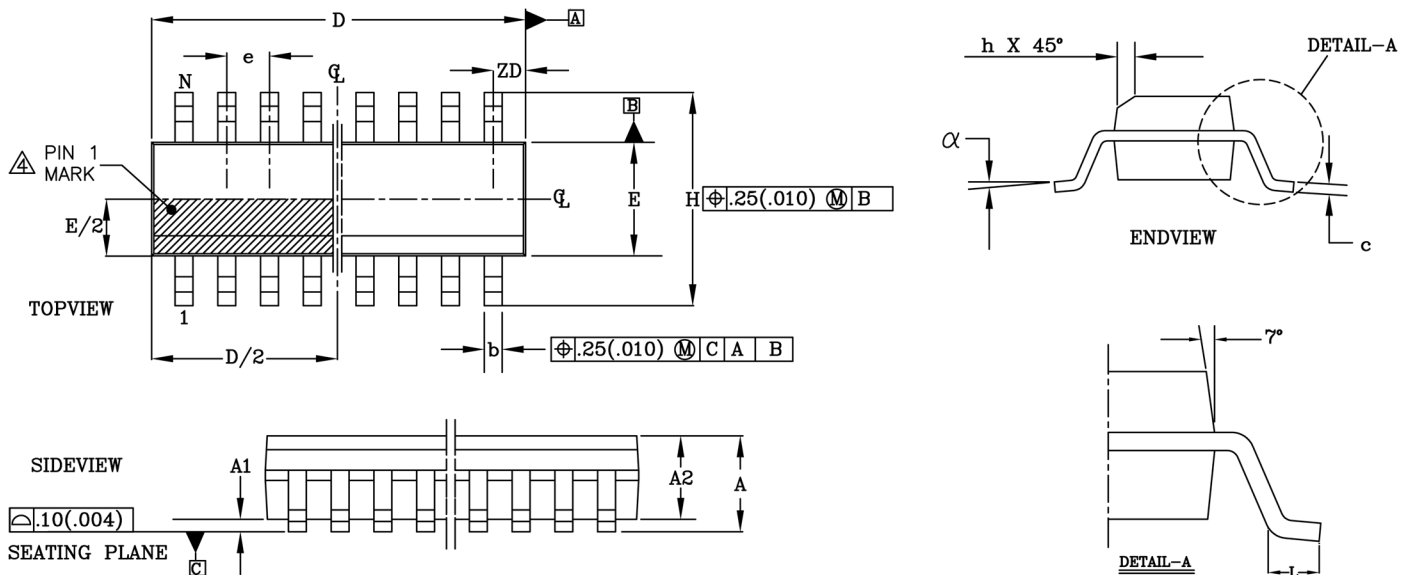


**Figure 5.** Driver High-Z Delay Waveforms

### Typical Performance Curves





**Package Dimensions (SOIC-16)**


SYMBOL	SOIC-16LD	
	MILLIMETERS	
	MIN	MAX
A1	0.10	0.25
B	0.36	0.46
C	0.19	0.25
D	9.80	9.98
E	3.81	3.99
e	1.27 BSC	
H	5.80	6.20
h	0.25	0.50
L	0.41	1.27
A	1.52	1.72
α	0°	8°
ZD	0.51 REF	
A2	1.37	1.57

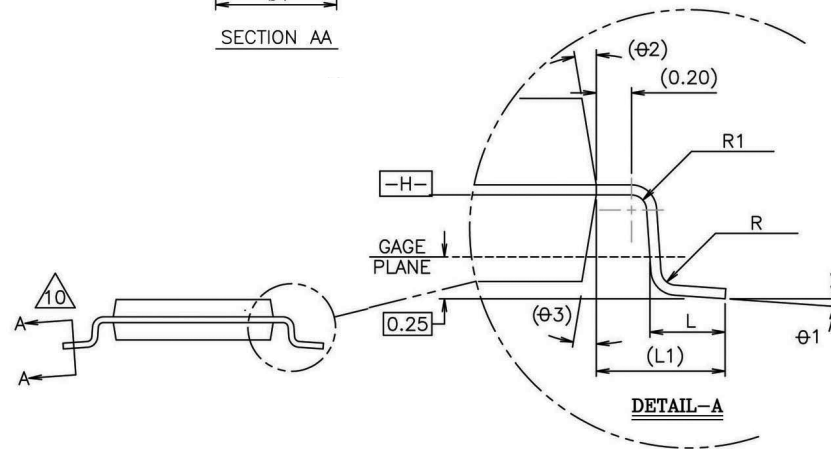
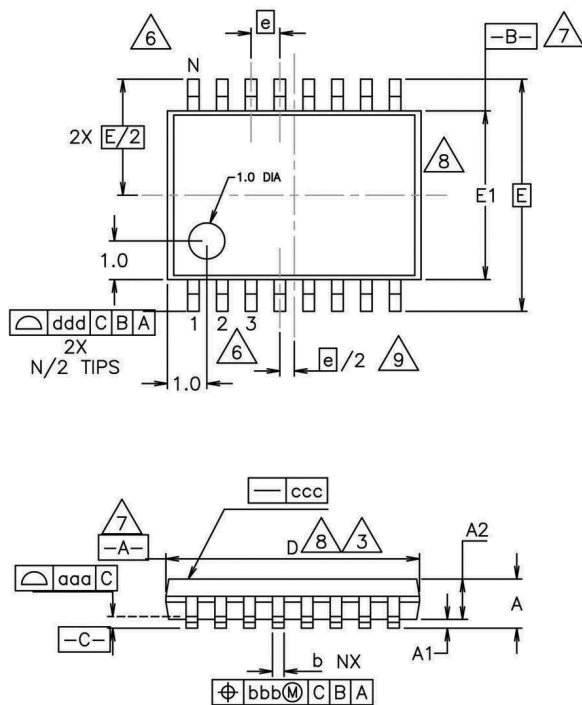
SYMBOL	SOIC-16LD	
	INCHES	
	MIN	MAX
A1	.0040	.0098
B	.014	.018
C	.0075	.0098
D	.386	.393
E	.150	.157
e	.050 BSC	
H	.2284	.2440
h	.0099	.0196
L	.016	.050
A	.060	.068
α	0°	8°
ZD	.020 REF	
A2	.054	.062

**NOTES :**

- LEAD COPLANARITY SHOULD BE 0 TO 0.10MM (.004") MAX.
- PACKAGE SURFACE FINISHING :  
(2.1) TOP : MATTE (CHARMILLES #18~30).
- ALL DIMENSIONS EXCLUDING MOLD FLASHES AND END FLASH FROM THE PACKAGE BODY SHALL NOT EXCEED 0.25MM (.010") PER SIDE(D).

△ DETAIL OF PIN #1 IDENTIFIER ARE OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED.

**Package Dimensions (TSSOP-16** Please contact support@telefunkensemi.com for availability)



	0.65mm LEAD PITCH			NOTE
	MIN	NOM	MAX	
A	---	---	1.10	---
A1	0.05	---	0.15	---
A2	0.85	0.90	0.95	---
L	0.50	0.60	0.75	---
R	0.09	---	---	---
R1	0.09	---	---	---
b	0.19	---	0.30	5
b1	0.19	0.22	0.25	---
c	0.09	---	0.20	---
c1	0.09	---	0.16	---
θ1	0°	---	8°	---
L1	1.0 REF			---
aaa	0.10			---
bbb	0.10			---
ccc	0.05			---
ddd	0.20			---
e	0.65 BSC			---
θ2	12° REF			---
θ3	12° REF			---
NOTE	7,2			
D	4.90	5.00	5.10	
E1	4.30	4.40	4.50	
E	6.4 BSC			
e	0.65 BSC			
N	16			

NOTES:

- ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- DIMENSION 'D' DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.
- DIMENSION 'E1' DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE.
- DIMENSION 'b' DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 MM TOTAL IN EXCESS OF THE 'b' DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD IS 0.07 MM FOR 0.5 MM PITCH PACKAGES.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DATUMS  $\square$ -A- AND  $\square$ -B- TO BE DETERMINED AT DATUM PLANE  $\square$ -H-
- DIMENSIONS 'D' AND 'E1' ARE TO BE DETERMINED AT DATUM PLANE  $\square$ -H-
- THIS DIMENSION APPLIES ONLY TO VARIATIONS WITH AN EVEN NUMBER OF LEADS PER SIDE. FOR VARIATION WITH AN ODD NUMBER OF LEADS PER SIDE, THE "CENTER" LEAD MUST BE COINCIDENT WITH THE PACKAGE CENTERLINE, DATUM A.
- CROSS SECTION A-A TO BE DETERMINED AT 0.10 TO 0.25 MM FROM THE LEAD TIP.
- THIS VARIATION IS NOT REGISTERED WITH JEDEC.
- PACKAGE SURFACE FINISHING:
  - TOP: MATTE (CHARMILLES: #18~30)
  - BOTTOM: MATTE (CHARMILLES: #12~27)

## Notes

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